

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, emplo

May 2017

FOD852

4-Pin DIP Photodarlington Output Optocoupler

Features

- High Current Transfer Ratio: 1000% Minimum
- · Safety and Regulatory Approvals
 - UL1577, 5,000 VAC_{RMS} for 1 Minute
 - DIN EN/IEC60747-5-5

Applications

- · Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs

Description

The FOD852 consists of gallium arsenide infrared emitting diode driving a silicon photodarlington output (with integral base-emitter resistor) in a 4-pin dual in-line package.

Functional Block Diagram

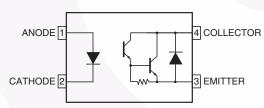


Figure 1. Schematic



Figure 2. Package Outlines

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

| Parameter | Characteristics | |
|--|------------------------|-----------|
| Installation Classifications per DIN VDE | < 150 V _{RMS} | I–IV |
| 0110/1.89 Table 1, For Rated Mains Voltage | < 300 V _{RMS} | I–III |
| Climatic Classification | | 30/110/21 |
| Pollution Degree (DIN VDE 0110/1.89) | | 2 |
| Comparative Tracking Index | | 175 |

| Symbol | Parameter | Value | Unit |
|-----------------------|--|--------------------|-------------------|
| V | Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC | 1360 | V _{peak} |
| V _{PR} | Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC | 1560 | V _{peak} |
| V _{IORM} | Maximum Working Insulation Voltage | 850 | V _{peak} |
| V _{IOTM} | Highest Allowable Over-Voltage | 6000 | V _{peak} |
| | External Creepage | ≥ 7 | mm |
| | External Clearance | ≥ 7 | mm |
| DTI | Distance Through Insulation (Insulation Thickness) | ≥ 0.4 | mm |
| T _S | Case Temperature ⁽¹⁾ | 175 | °C |
| I _{S,INPUT} | Input Current ⁽¹⁾ | 400 | mA |
| P _{S,OUTPUT} | Output Power ⁽¹⁾ | 700 | mW |
| R _{IO} | Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾ | > 10 ¹¹ | Ω |

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ Unless otherwise specified.

| Symbol | Parameter | Value | Units |
|------------------|--------------------------------|--------------------|-------|
| Total Device | | | |
| T _{STG} | Storage Temperature | -55 to +125 | °C |
| T _{OPR} | Operating Temperature | -30 to +100 | °C |
| TJ | Junction Temperature | -55 to +100 | °C |
| T _{SOL} | Lead Solder Temperature | 260 for 10 seconds | °C |
| P _{TOT} | Total Device Power Dissipation | 200 | mW |
| Input | | | |
| I _F | Continuous Forward Current | 50 | mA |
| V _R | Reverse Voltage | 6 | V |
| P _D | LED Power Dissipation | 70 | mW |
| Output | | | |
| V_{CEO} | Collector-Emitter Voltage | 300 | V |
| V _{ECO} | Emitter-Collector Voltage | 0.1 | V |
| I _C | Continuous Collector Current | 150 | mA |
| P _C | Collector Power Dissipation | 150 | mW |

Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.

Individual Component Characteristics

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|-------------------|-------------------------------------|---|------|------|------|------|
| Input | | | • | | | |
| V _F | Forward Voltage | I _F = 10 mA | | 1.2 | 1.4 | V |
| I _R | Reverse Current | V _R = 4 V | | | 10 | μA |
| C _t | Terminal Capacitance | V = 0, f = 1 kHz | | 30 | 250 | pF |
| Output | | | | | | |
| I _{CEO} | Collector Dark Current | V _{CE} = 200 V, I _F = 0 | | | 200 | nA |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_C = 0.1 \text{ mA}, I_F = 0$ | 300 | | | V |
| BV _{ECO} | Emitter-Collector Breakdown Voltage | $I_E = 10 \mu A, I_F = 0$ | 0.1 | | | V |

Transfer Characteristics

| Symbol | DC Characteristic | Test Conditions | Min. | Тур. | Max. | Unit |
|----------------------|---|---|-------|-------|--------|------|
| I _C | Collector Current | I _F = 1 mA, V _{CE} = 2 V | 10 | 40 | 150 | mΑ |
| CTR | Current Transfer Ratio ⁽²⁾ | IF = 1 IIIA, VCE = 2 V | 1,000 | 4,000 | 15,000 | % |
| V _{CE(SAT)} | Collector-Emitter Saturation Voltage | $I_F = 20 \text{ mA}, I_C = 100 \text{ mA}$ | | | 1.2 | ٧ |
| $f_{\mathbb{C}}$ | Cut-Off Frequency | V_{CE} = 2 V, I_{C} = 20 mA, R_{L} = 100 Ω , -3 dB | 1 | 7 | | kHz |
| t _R | Response Time (Rise) | $V_{CE} = 2 \text{ V, } I_{C} = 20 \text{ mA, } R_{I} = 100 \Omega$ | | 100 | 300 | μs |
| t _F | Response Time (Fall) | ACE - 5 A' IC - 50 HIN' IVE - 100 35 | | 20 | 100 | μs |

Isolation Characteristics

| Symbol | Characteristic | Test Conditions | Min. | Тур. | Max. | Units |
|---------------------------------------|--------------------------------|--|------|------------------|------|--------------------|
| V _{ISO} | Input-Output Isolation Voltage | $f = 60 \text{ Hz}, t = 1 \text{ minute}, I_{I-O} \le 2 \mu\text{A}$ | 5000 | | | VAC _{RMS} |
| R _{ISO} Isolation Resistance | | $V_{I-O} = 500 V_{DC}$ | | 10 ¹² | | Ω |
| C _{ISO} | Isolation Capacitance | V _{I-O} = 0, f = 1 MHz | | 0.6 | 1.0 | pf |

Note:

2. Current Transfer Ratio (CTR) = $I_C / I_F x$ 100%.

Typical Electrical/Optical Characteristic Curves

 $T_A = 25$ °C unless otherwise specified.

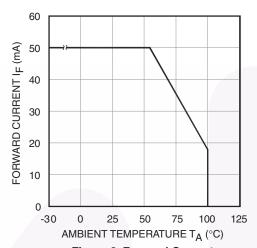
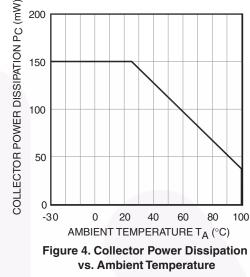


Figure 3. Forward Current vs. Ambient Temperature



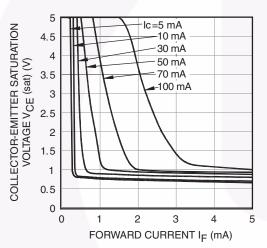


Figure 5. Collector-Emitted Saturation Voltage vs. Forward Current

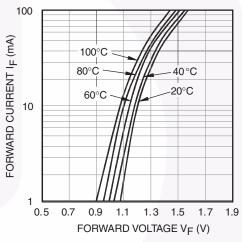


Figure 6. Forward Current vs. Forward Voltage

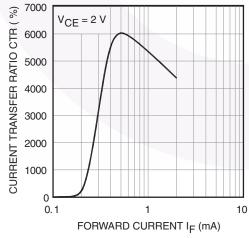


Figure 7. Current Transfer Ratio vs. Forward Current

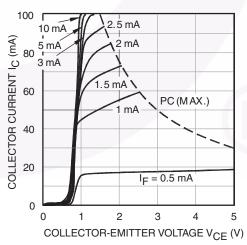


Figure 8. Collector Current vs. Collector-Emitter Voltage

Typical Electrical/Optical Characteristic Curves (Continued)

 $T_A = 25$ °C unless otherwise specified.

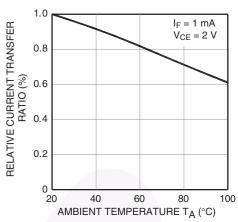
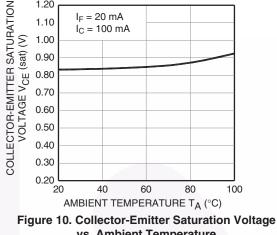


Figure 9. Relative Current Transfer Ratio vs. Ambient Temperature



1.20

vs. Ambient Temperature

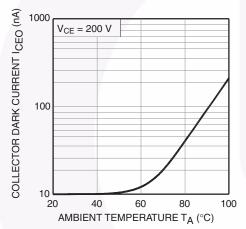


Figure 11. Collector Dark Current vs. Ambient Temperature

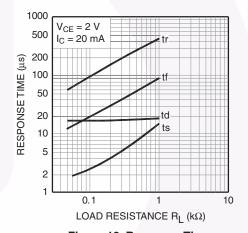


Figure 12. Response Time vs. Load Resistance

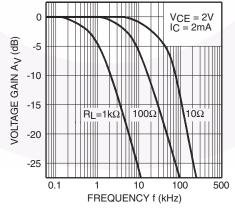


Figure 13. Frequency Response

Test Circuits

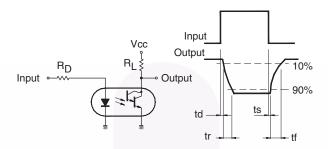


Figure 14. Test Circuit for Response Time

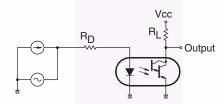
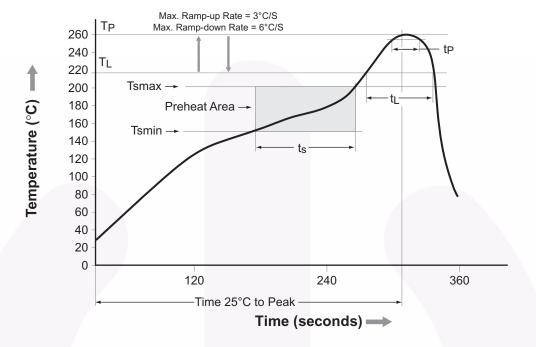


Figure 15. Test Circuit for Frequency Response

Reflow Profile



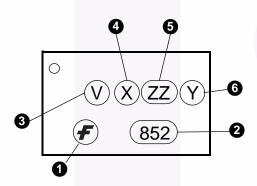
| Profile Feature | Pb-Free Assembly Profile | | |
|---|--------------------------|--|--|
| Temperature Min. (Tsmin) | 150°C | | |
| Temperature Max. (Tsmax) | 200°C | | |
| Time (t _S) from (Tsmin to Tsmax) | 60–120 seconds | | |
| Ramp-up Rate (t _L to t _P) | 3°C/second max. | | |
| Liquidous Temperature (T _L) | 217°C | | |
| Time (t _L) Maintained Above (T _L) | 60-150 seconds | | |
| Peak Body Package Temperature | 260°C +0°C / -5°C | | |
| Time (t _P) within 5°C of 260°C | 30 seconds | | |
| Ramp-down Rate (T _P to T _L) | 6°C/second max. | | |
| Time 25°C to Peak Temperature | 8 minutes max. | | |

Figure 16. Reflow Profile

Ordering Information

| Part Number | Package | Packing Method |
|-------------|--|--------------------------------------|
| FOD852 | DIP 4-Pin | Tube (100 units per tube) |
| FOD852S | SMT 4-Pin (Lead Bend) | Tube (100 units per tube) |
| FOD852SD | SMT 4-Pin (Lead Bend) | Tape and Reel (1,000 units per reel) |
| FOD852300 | DIP 4-Pin, DIN EN/IEC60747-5-5 option | Tube (100 units per tube) |
| FOD8523S | SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option | Tube (100 units per tube) |
| FOD8523SD | SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option | Tape and Reel (1,000 units per reel) |
| FOD852300W | DIP 4-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 option | Tube (100 units per tube) |

Marking Information



| Definiti | ons | |
|----------|---|--|
| 1 | Fairchild Logo | |
| 2 | Device Number | |
| 3 | DIN EN/IEC60747-5-5 Option (only appears on parts ordered with this option) | |
| 4 | One-Digit Year Code, e.g., '5' | |
| 5 | Two-Digit Work Week, Ranging from '01' to '53' | |
| 6 | Assembly Package Code Y = Manufactured in Thailand YA = Manufactured in China | |

Carrier Tape Specifications

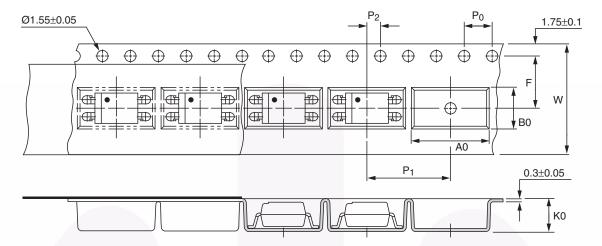
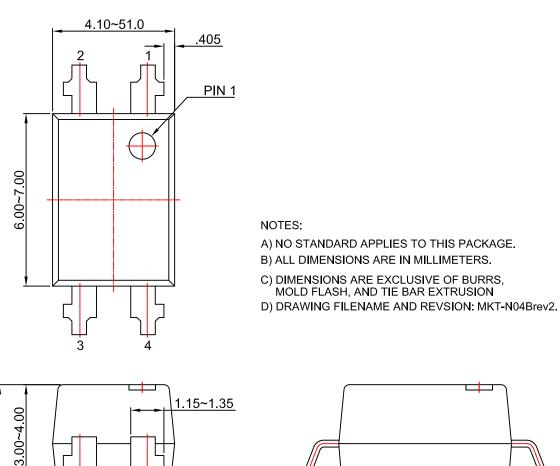
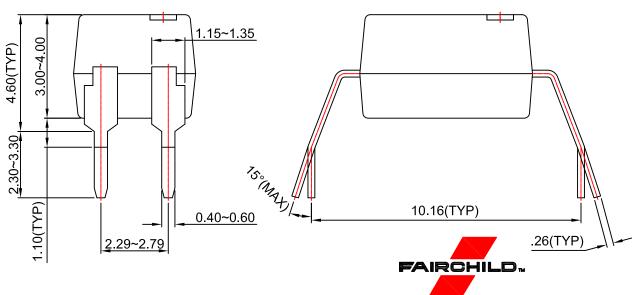
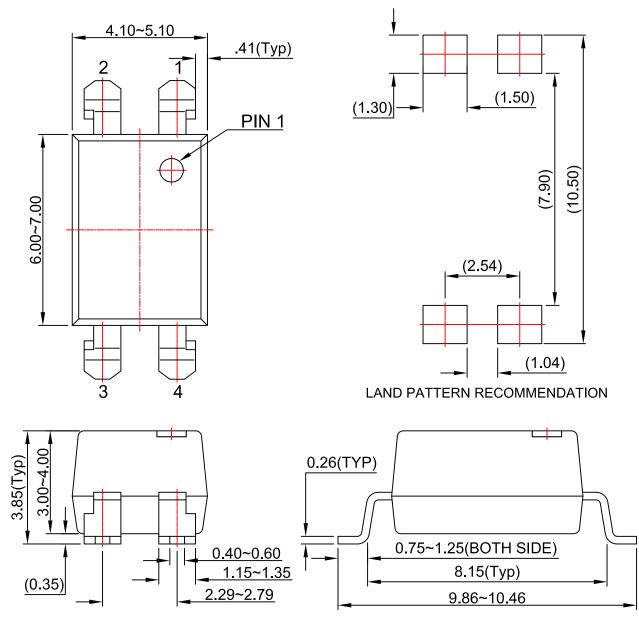


Figure 17. Carrier Tape Specification

| Symbol | Description | Dimensions in mm (inches) |
|---------------------|--|--------------------------------------|
| W | Tape wide | 16 ± 0.3 (0.63) |
| P ₀ | Pitch of sprocket holes | 4 ± 0.1 (0.15) |
| F P ₂ | Distance of compartment | 7.5 ± 0.1 (0.295) 2 ± 0.1 (0.079) |
| P ₁ | Distance of compartment to compartment | 12 ± 0.1 (0.472) |
| A0 | Compartment | 10.45 ± 0.1 (0.411) |
| В0 | | 5.30 ± 0.1 (0.209) |
| K0 | | 4.25 ± 0.1 (0.167) |



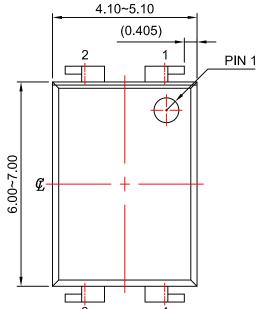




NOTES:

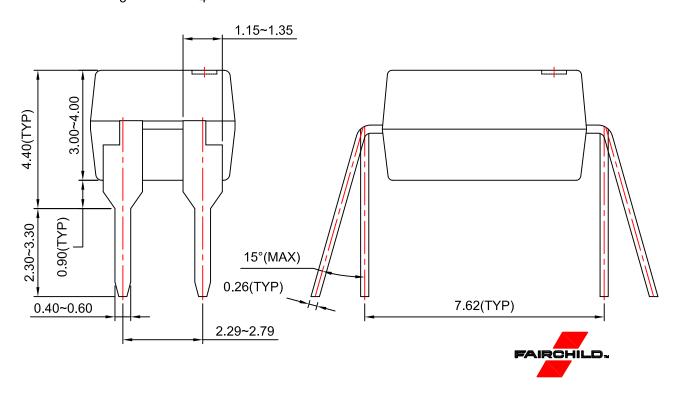
- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVSION: MKT-N04Crev2.





NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVSION: MKT-N04Arev2.



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see any inability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and ex

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative